RJK03P6DPA

MOS1 30 V, 15 A, 9.4 mΩ max.
MOS2 30 V, 45 A, 2.4 mΩ max.
Built in SBD Dual N-channel Power MOS FET
High Speed Power Switching

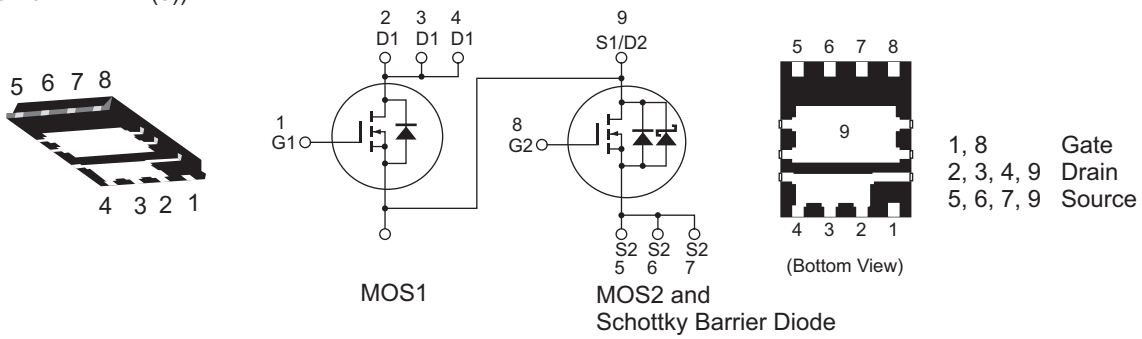
R07DS0905EJ0110
Rev.1.10
Nov 01, 2012

Features

- Low on-resistance
- Capable of 4.5 V gate drive
- High density mounting
- Pb-free
- Halogen-free

Outline

RENESAS Package code: PWSN0008DD-B
(Package name: WPAK-D(3))



Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings		Unit
		MOS1	MOS2	
Drain to source voltage	V_{DSS}	30	30	V
Gate to source voltage	V_{GSS}	±20	±20	V
Drain current	I_D	15	45	A
Drain peak current	$I_{D(pulse)}$ Note1	60	180	A
Reverse drain current	I_{DR}	15	45	A
Avalanche current	I_{AP} Note 2	8.5	19	A
Avalanche energy	E_{AS} Note 2	7.23	36.1	mJ
Channel dissipation	Pch Note3	10	30	W
Channel temperature	Tch	150	150	°C
Storage temperature	Tstg	–55 to +150	–55 to +150	°C

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%
2. Value at Tch = 25°C, Rg ≥ 50 Ω
3. Tc=25°C

Electrical Characteristics

• MOS1

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	30	—	—	V	I_D = 10 mA, V_{GS} = 0
Gate to source leak current	I_{GSS}	—	—	±0.5	μA	V_{GS} = ±20 V, V_{DS} = 0
Zero gate voltage drain current	I_{DSS}	—	—	1	μA	V_{DS} = 24 V, V_{GS} = 0
Gate to source cutoff voltage	$V_{GS(off)}$	1.2	—	2.5	V	V_{DS} = 10 V, I_D = 1 mA
Static drain to source on state resistance	$R_{DS(on)}$	—	7.8	9.4	mΩ	I_D = 7.5 A, V_{GS} = 10 V Note4
	$R_{DS(on)}$	—	9.7	12.6	mΩ	I_D = 7.5 A, V_{GS} = 4.5 V Note4
Forward transfer admittance	$\|y_{fs}\|$	—	36	—	S	I_D = 7.5 A, V_{DS} = 5 V Note4
Input capacitance	Ciss	—	850	1190	pF	V_{DS} = 10 V
Output capacitance	Coss	—	150	—	pF	V_{GS} = 0
Reverse transfer capacitance	Crss	—	80	—	pF	f = 1MHz
Gate Resistance Note5	Rg	—	1.55	3.1	Ω	
Total gate charge Note5	Qg	—	7.1	—	nC	V_{DD} = 10 V
Gate to source charge	Qgs	—	2.3	—	nC	V_{GS} = 4.5 V
Gate to drain charge	Qgd	—	2.0	—	nC	I_D = 15 A
Turn-on delay time	$t_{d(on)}$	—	2.8	—	ns	V_{GS} =10 V, I_D = 7.5 A
Rise time Note5	t_r	—	1.7	—	ns	V_{DD} ≈ 10 V
Turn-off delay time	$t_{d(off)}$	—	12.6	—	ns	R_L = 1.3 Ω
Fall time	t_f	—	3.5	—	ns	R_g = 4.7 Ω
Body–drain diode forward voltage	V_{DF}	—	0.84	1.09	V	IF = 15 A, V_{GS} = 0 Note4
Body–drain diode reverse recovery time	t_{rr}	—	8.1	—	ns	IF =15 A, V_{GS} = 0 di_F/ dt = 500 A/μs

Notes: 4. Pulse test

• MOS2

(Ta = 25°C)

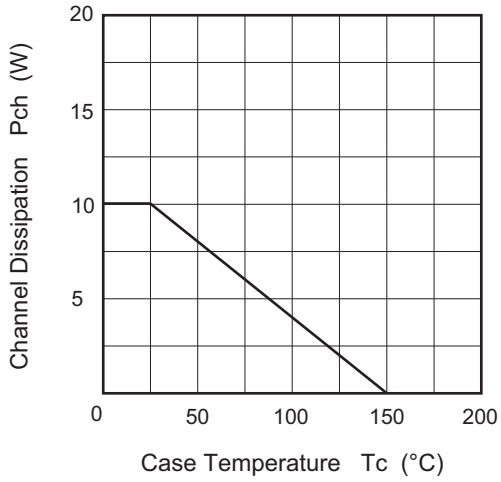
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	30	—	—	V	I_D = 10 mA, V_{GS} = 0
Gate to source leak current	I_{GSS}	—	—	±0.5	μA	V_{GS} = ±20 V, V_{DS} = 0
Zero gate voltage drain current	I_{DSS}	—	—	1	mA	V_{DS} = 24 V, V_{GS} = 0
Gate to source cutoff voltage	$V_{GS(off)}$	1.2	—	2.5	V	V_{DS} = 10 V, I_D =1 mA
Static drain to source on state resistance	$R_{DS(on)}$	—	2.0	2.4	mΩ	I_D =22.5 A, V_{GS} = 10 V Note4
	$R_{DS(on)}$	—	2.4	3.2	mΩ	I_D = 22.5 A, V_{GS} = 4.5 V Note4
Forward transfer admittance	$\|y_{fs}\|$	—	114	—	S	I_D = 22.5 A, V_{DS} = 5 V Note4
Input capacitance	Ciss	—	3780	5290	pF	V_{DS} = 10 V
Output capacitance	Coss	—	630	—	pF	V_{GS} = 0
Reverse transfer capacitance	Crss	—	375	—	pF	f = 1MHz
Gate Resistance	Rg	—	1.5	3.0	Ω	
Total gate charge	Qg	—	29.4	—	nC	V_{DD} = 10 V
Gate to source charge	Qgs	—	9.6	—	nC	V_{GS} = 4.5 V
Gate to drain charge	Qgd	—	10.0	—	nC	I_D = 45 A
Turn-on delay time	$t_{d(on)}$	—	6.7	—	ns	V_{GS} = 10 V, I_D = 22.5 A
Rise time	t_r	—	4.6	—	ns	V_{DD} ≈ 10 V
Turn-off delay time	$t_{d(off)}$	—	66.8	—	ns	R_L = 0.44 Ω
Fall time	t_f	—	21.5	—	ns	R_g = 4.7 Ω
Schottky Barrier diode forward voltage	V_F	—	0.40	—	V	IF = 2 A, V_{GS} = 0 Note4
Body–drain diode reverse recovery time	t_{rr}	—	9.4	—	ns	IF = 45 A, V_{GS} = 0 di_F/ dt = 500 A/μs

Notes: 4. Pulse test

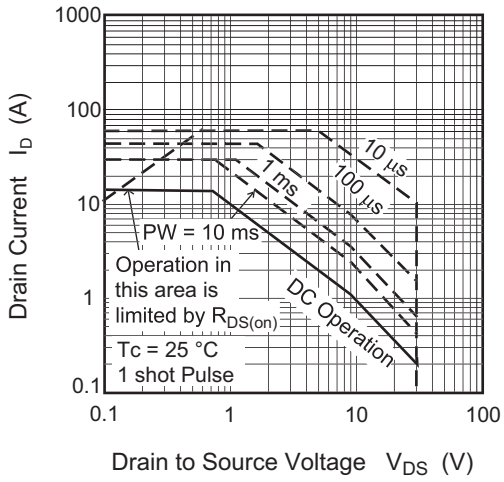
Main Characteristics

• MOS1

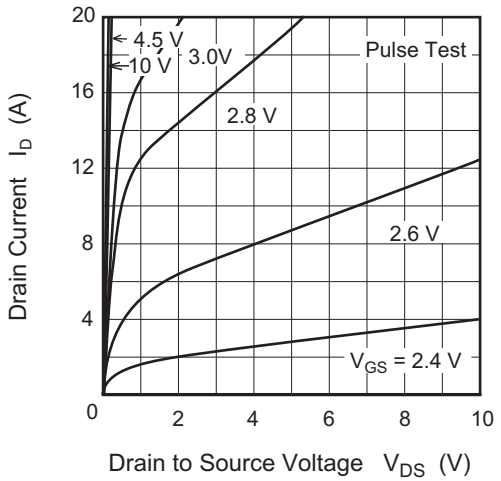
Power vs. Temperature Derating



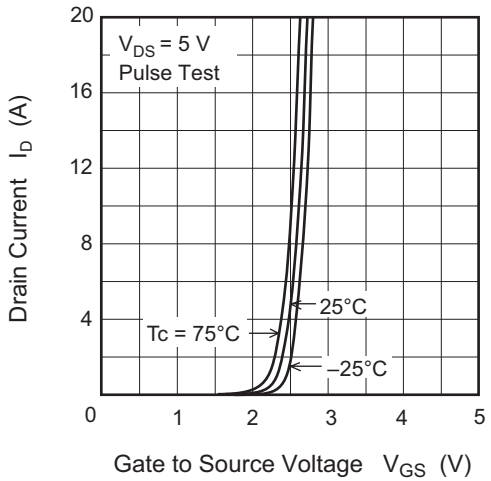
Maximum Safe Operation Area



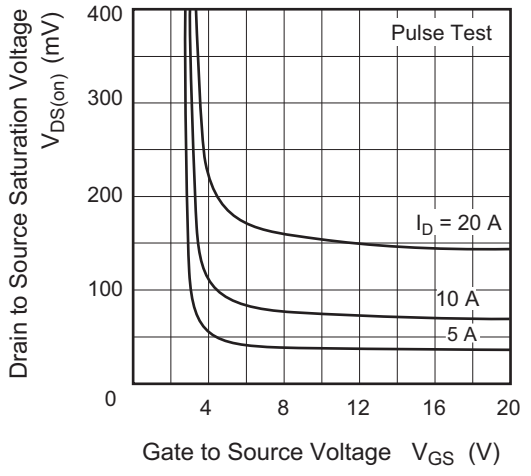
Typical Output Characteristics



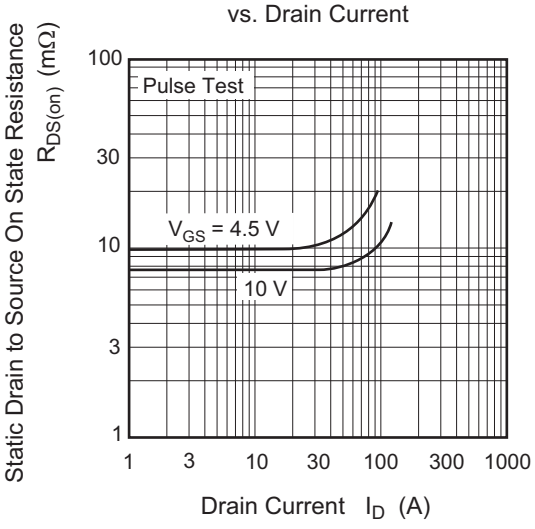
Typical Transfer Characteristics



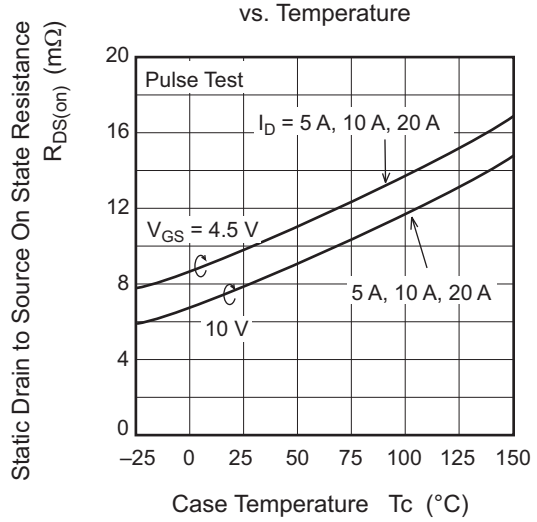
Drain to Source Saturation Voltage vs. Gate to Source Voltage



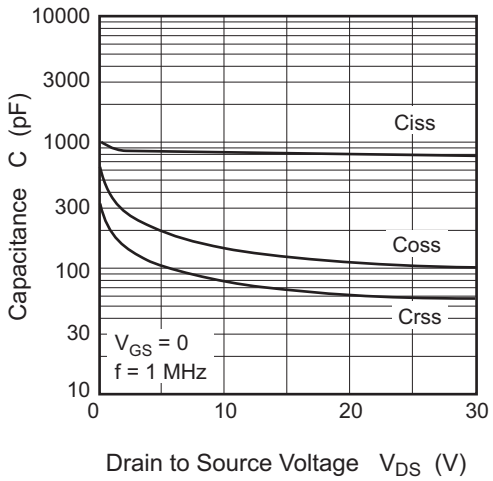
Static Drain to Source On State Resistance vs. Drain Current



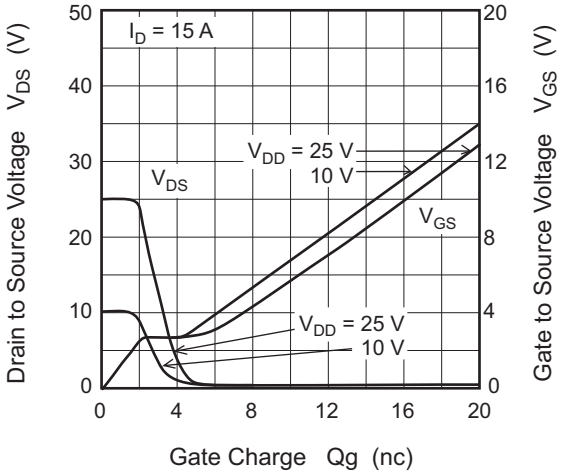
Static Drain to Source On State Resistance vs. Temperature



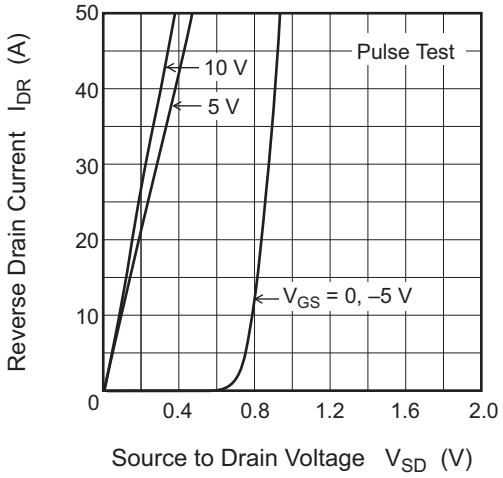
Typical Capacitance vs. Drain to Source Voltage



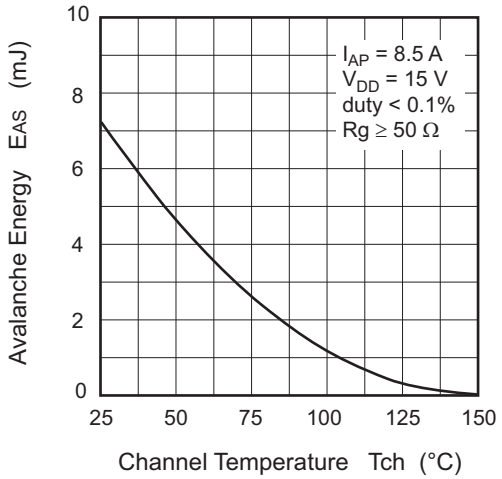
Dynamic Input Characteristics



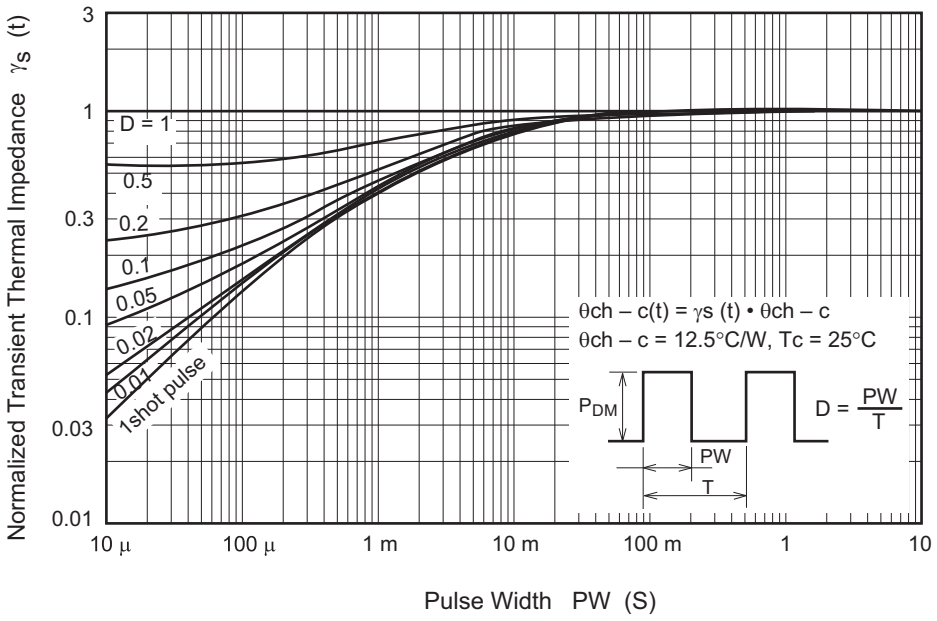
Reverse Drain Current vs. Source to Drain Voltage



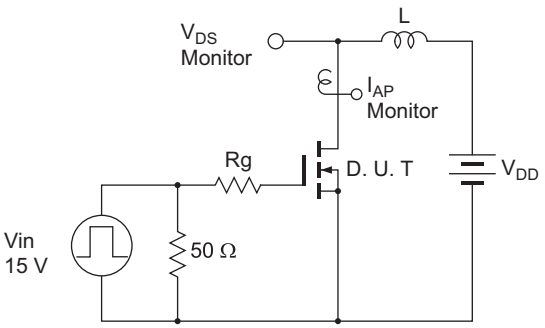
Maximum Avalanche Energy vs. Channel Temperature Derating



Normalized Transient Thermal Impedance vs. Pulse Width

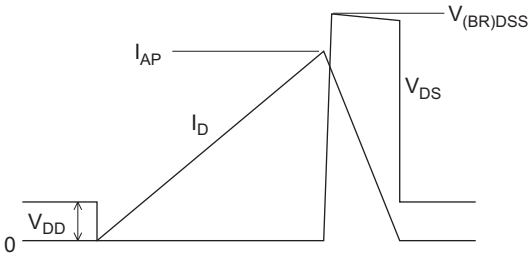


Avalanche Test Circuit

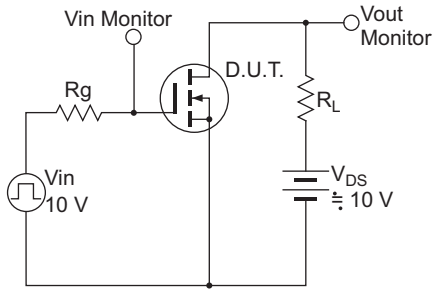


Avalanche Waveform

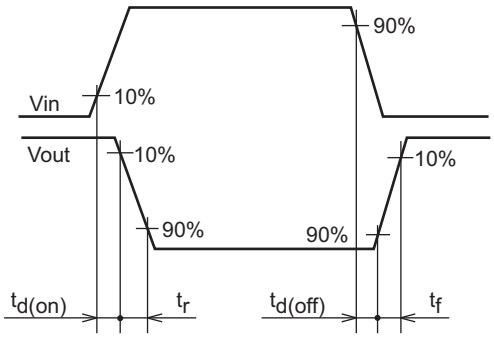
$$E_{AS} = \frac{1}{2} L \bullet I_{AP}^2 \bullet \frac{V_{DSS}}{V_{DSS} - V_{DD}}$$



Switching Time Test Circuit

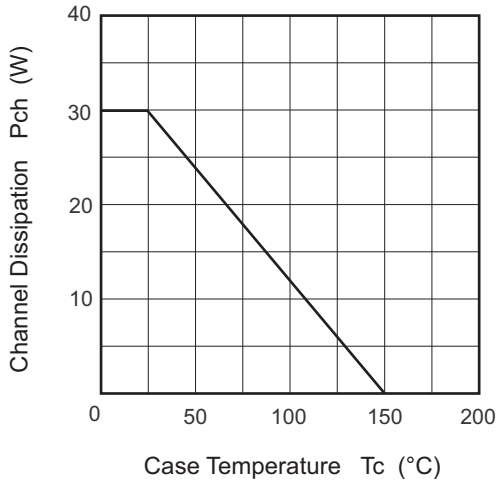


Switching Time Waveform

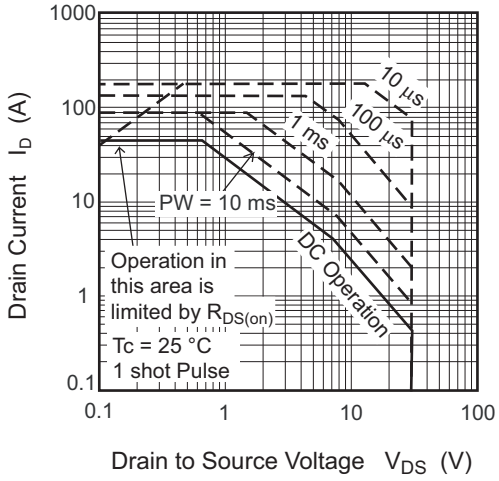


• MOS2 and Schottky Barrier Diode

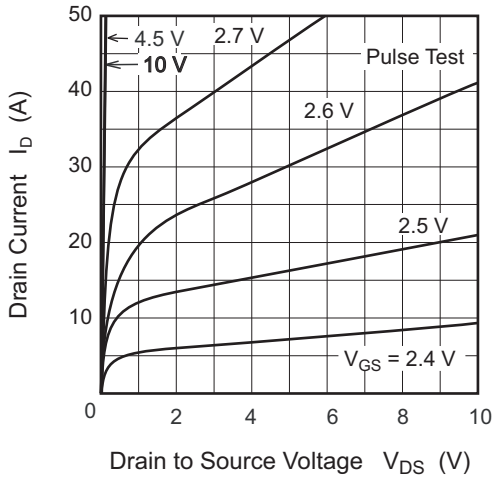
Power vs. Temperature Derating



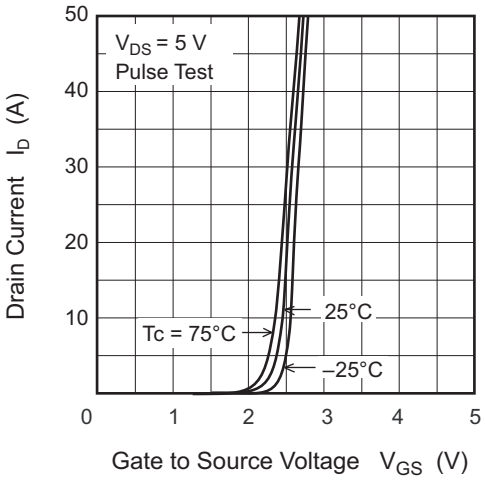
Maximum Safe Operation Area



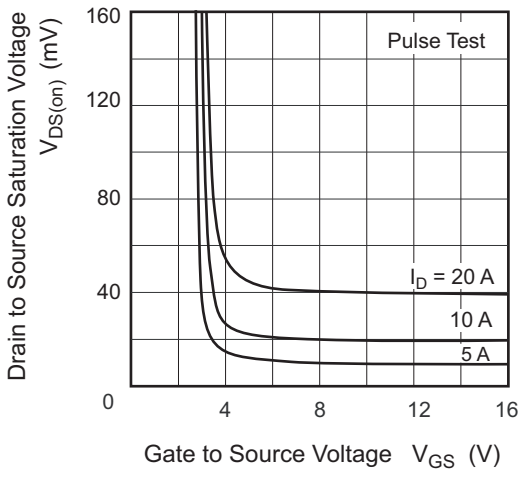
Typical Output Characteristics



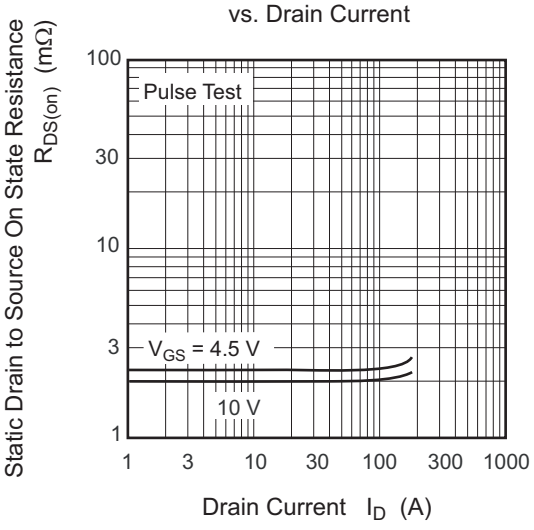
Typical Transfer Characteristics



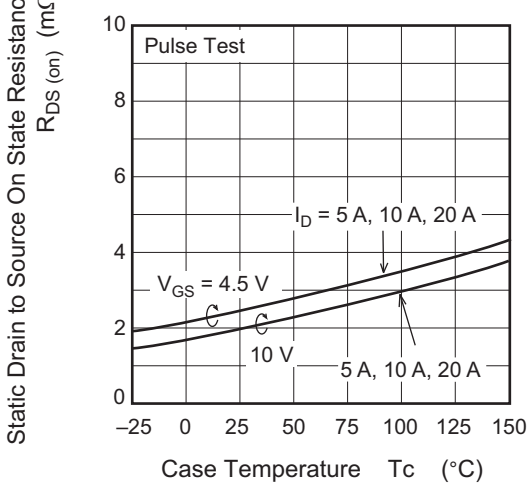
Drain to Source Saturation Voltage vs. Gate to Source Voltage



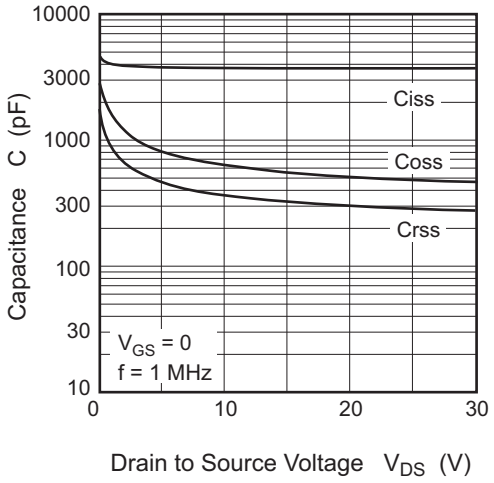
Static Drain to Source On State Resistance vs. Drain Current



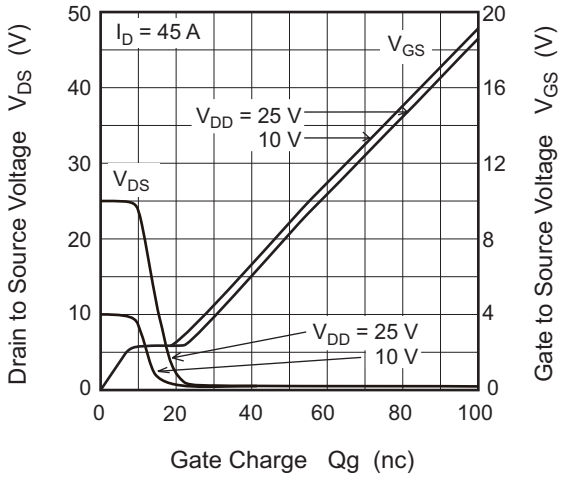
Static Drain to Source On State Resistance vs. Temperature



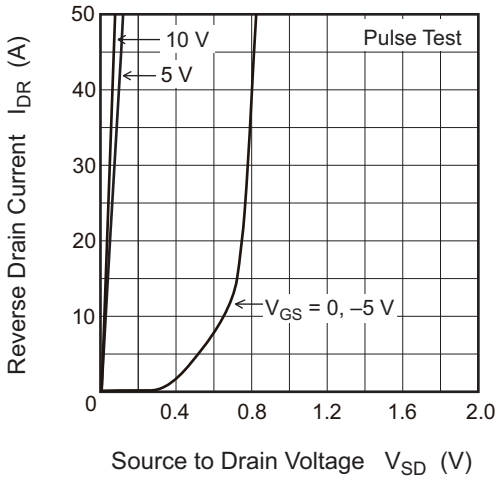
Typical Capacitance vs. Drain to Source Voltage



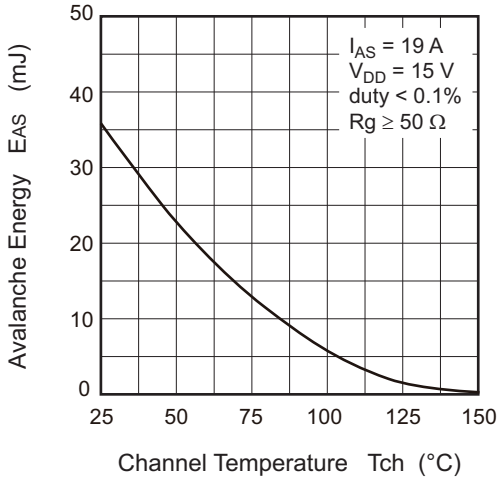
Dynamic Input Characteristics



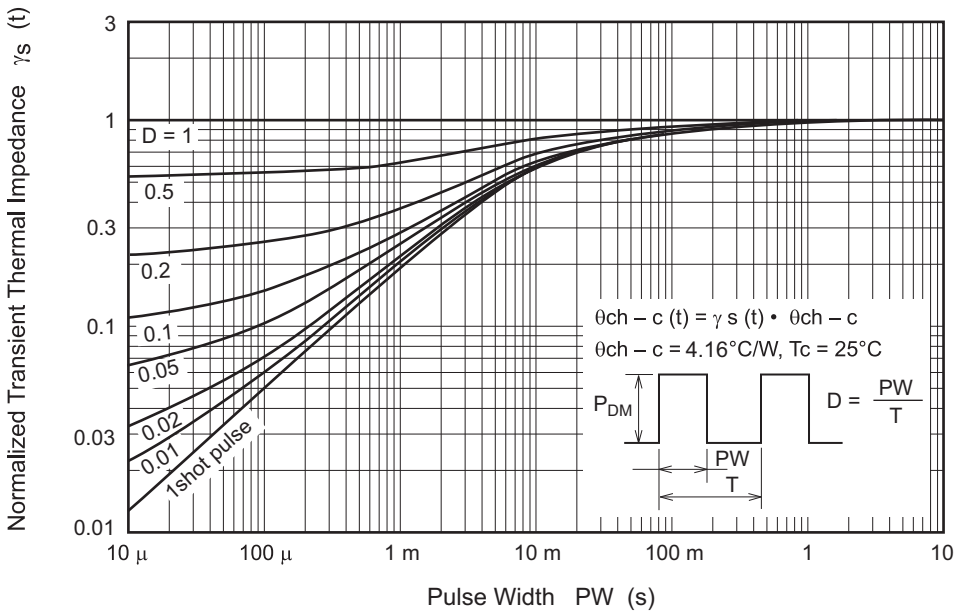
Reverse Drain Current vs. Source to Drain Voltage



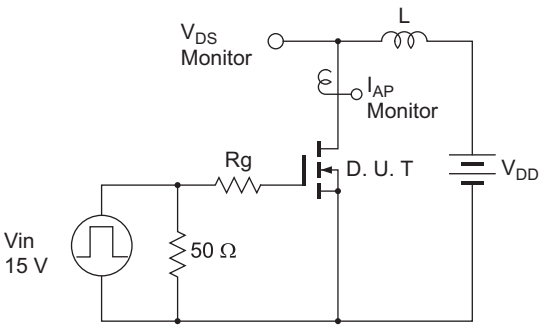
Maximum Avalanche Energy vs. Channel Temperature Derating



Normalized Transient Thermal Impedance vs. Pulse Width

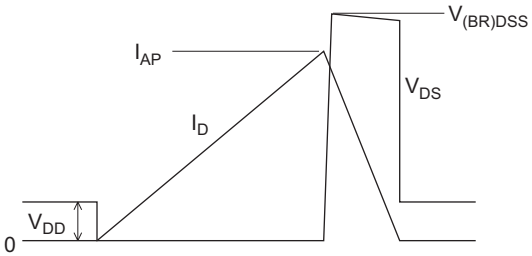


Avalanche Test Circuit

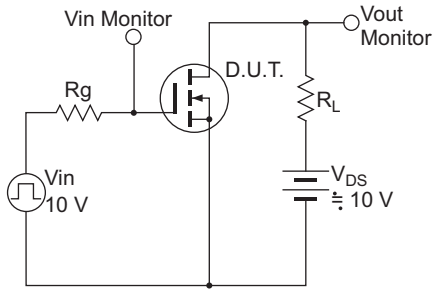


Avalanche Waveform

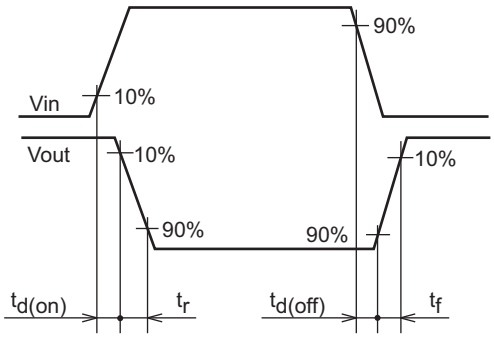
$$E_{AS} = \frac{1}{2} L \bullet I_{AP}^2 \bullet \frac{V_{DSS}}{V_{DSS} - V_{DD}}$$



Switching Time Test Circuit



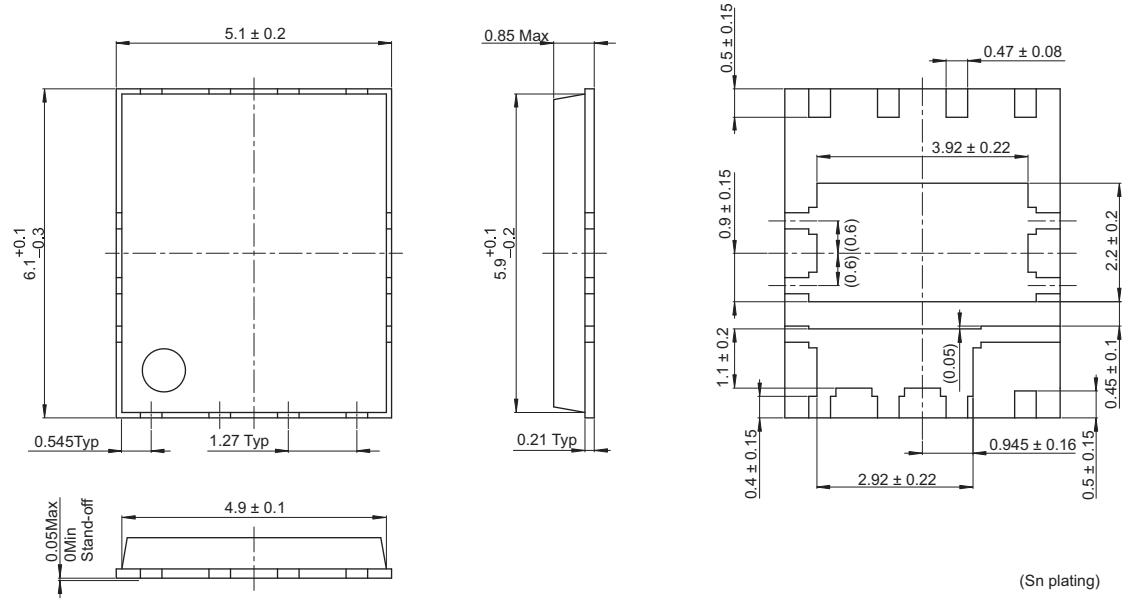
Switching Time Waveform



Package Dimensions

Package Name	JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
WPAK-D(3)	—	PWSN0008DD-B	WPAK-D(3)V	0.07g

Unit : mm



Ordering Information

Orderable Part Number	Quantity	Shipping Container
RJK03P6DPA-00-J5A	3000 pcs	Taping

Note: The symbol of 2nd "-" is occasionally presented as "#".

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Renesas Electronics America Inc.
2880 Scott Boulevard Santa Clara, CA 95050-2554, U.S.A.
Tel: +1-408-588-6000, Fax: +1-408-588-6130

Renesas Electronics Canada Limited
1101 Nicholson Road, Newmarket, Ontario L3Y 9C3, Canada
Tel: +1-905-898-5441, Fax: +1-905-898-3220

Renesas Electronics Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K
Tel: +44-1628-651-700, Fax: +44-1628-651-804

Renesas Electronics Europe GmbH
Arcadiastrasse 10, 40472 Düsseldorf, Germany
Tel: +49-211-65030, Fax: +49-211-6503-1327

Renesas Electronics (China) Co., Ltd.
7th Floor, Quantum Plaza, No.27 ZhiChunLu Haidian District, Beijing 100083, P.R.China
Tel: +86-10-8235-1155, Fax: +86-10-8235-7679

Renesas Electronics (Shanghai) Co., Ltd.
Unit 204, 205, AZIA Center, No.1233 Lujiazui Ring Rd., Pudong District, Shanghai 200120, China
Tel: +86-21-5877-1818, Fax: +86-21-6887-7858 / -7898

Renesas Electronics Hong Kong Limited
Unit 1601-1613, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong
Tel: +852-2886-9318, Fax: +852 2886-9022/9044

Renesas Electronics Taiwan Co., Ltd.
13F, No. 363, Fu Shing North Road, Taipei, Taiwan
Tel: +886-2-8175-9600, Fax: +886 2-8175-9670

Renesas Electronics Singapore Pte. Ltd.
80 Bendemeer Road, Unit #06-02 Hyflux Innovation Centre Singapore 339949
Tel: +65-6213-0200, Fax: +65-6213-0300

Renesas Electronics Malaysia Sdn.Bhd.
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No. 18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: +60-3-7955-9390, Fax: +60-3-7955-9510

Renesas Electronics Korea Co., Ltd.
11F., Samik Lavied' or Bldg., 720-2 Yeoksam-Dong, Kangnam-Ku, Seoul 135-080, Korea
Tel: +82-2-558-3737, Fax: +82-2-558-5141

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